

4. The semiconductor device according to claim 2, wherein said capacitance element includes two conductive layers and a dielectric material layer, said two conductive layers positioned apart from each other on said insulating film, and said dielectric layer is formed in the clearance between the two

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10. The semiconductor device according to claim 1,

[illegible]

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forming at least one thin film passive element including at least one conductive layer on said insulating film;

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forming a dielectric material layer on said first  
conductive layer; and

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forming two pieces of conductive layer positioned adjacent to each other a predetermined distance apart from each other on said insulating film; and

[illegible]

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20. The method of manufacturing a semiconductor device according to claim 19, wherein said forming of the inductance element comprises patterning said conductive layer in any of the shapes selected from the group consisting of an angular eddy shape, a rectangular wave shape and a loop shape.

21. The method of manufacturing a semiconductor device according to claim 20, wherein said forming of the inductance element comprises forming a magnetic

film on said conductive layer.

22. The method of manufacturing a semiconductor device according to claim 14, wherein said forming of said thin film passive element comprises covering the periphery of said thin film passive element with a protective film.

23. The method of manufacturing a semiconductor device according to claim 14, wherein said forming of said thin film passive element comprises forming said columnar electrode in at least one of the electrode terminals at one end and the other end of said thin film passive element.

24. The method of manufacturing a semiconductor device according to claim 14, wherein said forming of said thin film passive element comprises connecting at least one of the electrode terminals at one end and the other end of said thin film passive element to said connection pad.

25. The method of manufacturing a semiconductor device according to claim 14, wherein said forming of said thin film passive element comprises connecting each electrode terminal of said thin film passive element to at least one of said connection pad and said columnar electrode.